

Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

Vishay/Siliconix SI5433BDC-T1-E3

For any questions, you can email us directly: sales@integrated-circuit.com

Datasheet of SI5433BDC-T1-E3 - MOSFET P-CH 20V 4.8A 1206-8

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



Si5433BDC

Vishay Siliconix

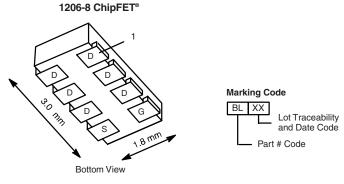
P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)		
- 20	0.037 at V _{GS} = - 4.5 V	- 6.7			
	0.050 at V _{GS} = - 2.5 V	- 5.9	15		
	0.070 at V _{GS} = - 1.8 V	- 5.0			

FEATURES

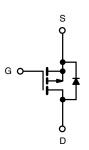
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET





Ordering Information: Si5433BDC-T1-E3 (Lead (Pb)-free)

Si5433BDC-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T	A = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		V
Gate-Source Voltage		V _{GS}	± 8		
O-ation David Onesat /T 450,0008	T _A = 25 °C	- I _D	- 6.7	- 4.8	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C		- 4.8	- 3.5	A
Pulsed Drain Current		I _{DM}	- 20		Α
Continuous Source Current ^a		I _S	- 2.1	- 1.1	
Mariana Baran Birata di a	T _A = 25 °C	P _D	2.5	1.3	W
Maximum Power Dissipation ^a	T _A = 85 °C		1.3	0.7	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Marrian Incation to Austriant	t ≤ 5 s	R _{thJA}	45	50	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		85	95		
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	20		

Notes

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

Document Number: 73208 S-83054-Rev. B, 29-Dec-08

Datasheet of SI5433BDC-T1-E3 - MOSFET P-CH 20V 4.8A 1206-8

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

Si5433BDC

Vishay Siliconix



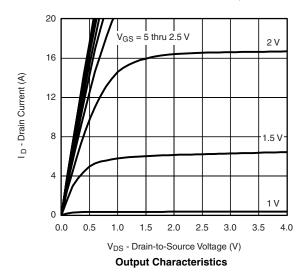
Parameter Symbol		Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage V _{GS}		$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.45		- 1.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1		
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 85 °C			- 5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -4.8 \text{ A}$		0.030	0.037	Ω	
		$V_{GS} = -2.5 \text{ V}, I_D = -4.2 \text{ A}$		0.041	0.050		
		V _{GS} = - 1.8 V, I _D = - 1 A		0.056	0.070		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 4.8 A		18		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.1 A, V _{GS} = 0 V		- 0.8	- 1.2	٧	
Dynamic ^b							
Total Gate Charge	Qg			15	22		
Gate-Source Charge	Q _{gs} Q _{gd}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.8 \text{ A}$		2.4		nC	
Gate-Drain Charge				3.6			
Gate Resistance	R_g			10		Ω	
Turn-On Delay Time	t _{d(on)}			12	25		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		25	40	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		80	120		
Fall Time	t _f			55	85		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.1 A, dl/dt = 100 A/μs		30	60		

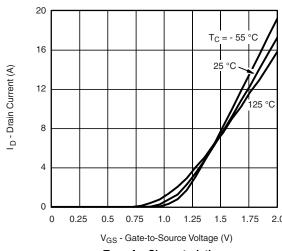
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Transfer Characteristics

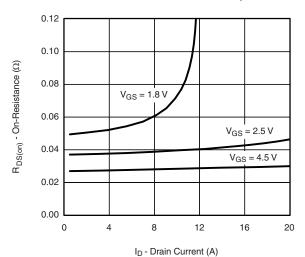




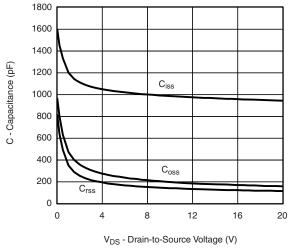
Si5433BDC

Vishay Siliconix

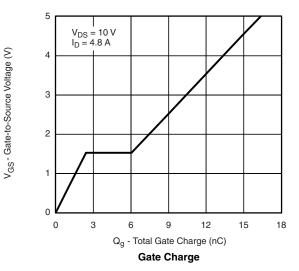
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current





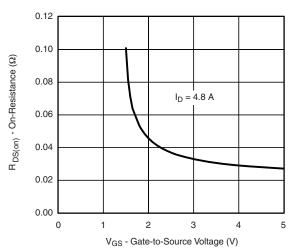


20 T_J = 150 °C 10 T_J = 25 °C 0.0 0.2 0.4 0.6 0.8 1.0 1.2 V_{SD} - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

1.6 $V_{GS} = 4.5 \text{ V}$ $I_D = 4.8 \text{ A}$ 1.4 R_{DS(on)} - On-Resistance (Normalized) 1.2 1.0 0.8 0.6 150 - 50 - 25 25 50 75 100 125 T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

Document Number: 73208 S-83054-Rev. B, 29-Dec-08

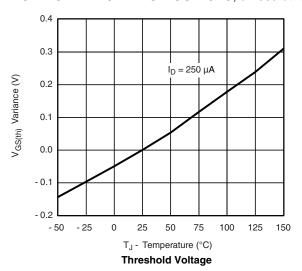
Is - Source Current (A)

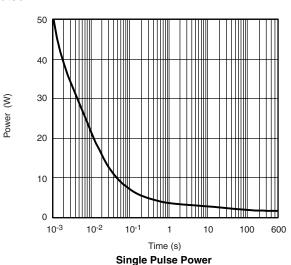
Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

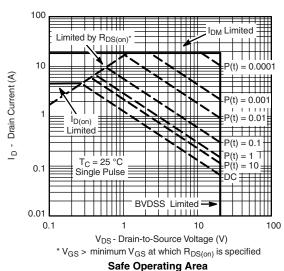
Si5433BDC

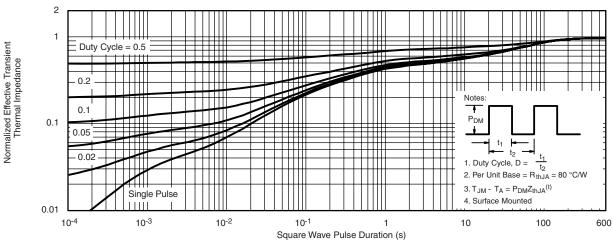
Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted









Normalized Thermal Transient Impedance, Junction-to-Ambient



Datasheet of SI5433BDC-T1-E3 - MOSFET P-CH 20V 4.8A 1206-8

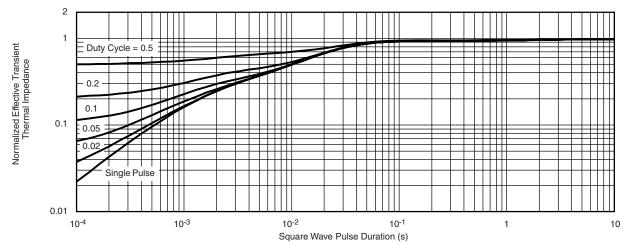
Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



Si5433BDC

Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73208.

Document Number: 73208 www.vishay.com S-83054-Rev. B, 29-Dec-08 5



Datasheet of SI5433BDC-T1-E3 - MOSFET P-CH 20V 4.8A 1206-8

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



Legal Disclaimer Notice

Vishav

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Revision: 13-Jun-16 1 Document Number: 91000